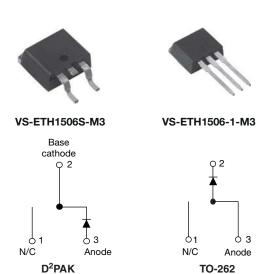


VS-ETH1506SHM3, VS-ETH1506-1HM3

Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt®



www.vishay.com

| PRODUCT SUMMARY | | | | |
|----------------------------------|---|--|--|--|
| Package | TO-263AB (D ² PAK), TO-262AA | | | |
| I _{F(AV)} | 15 A | | | |
| V_{R} | 600 V | | | |
| V _F at I _F | 2.45 V | | | |
| t _{rr} (typ.) | 21 ns | | | |
| T _J max. | 175 °C | | | |
| Diode variation | Single die | | | |

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912







ROHS COMPLIANT HALOGEN FREE

DESCRIPTION/APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS |
| Repetitive peak reverse voltage | V _{RRM} | | 600 | V |
| Average rectified forward current | I _{F(AV)} | T _C = 139 °C | 15 | А |
| Non-repetitive peak surge current | I _{FSM} | T _C = 25 °C | 160 | A |
| Operating junction and storage temperatures | T _J , T _{Stg} | | - 65 to 175 | °C |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|--|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 600 | - | - | |
| Forward voltage V _F | I _F = 15A | - | 1.8 | 2.45 | V | |
| | I _F = 15 A, T _J = 150 °C | - | 1.25 | 1.6 | | |
| Reverse leakage current | | $V_R = V_R$ rated | - | 0.01 | 15 | |
| neverse leakage current | I _R | $T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$ | - | 20 | 200 | μΑ |
| Junction capacitance | C _T | V _R = 600 V | - | 12 | - | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH |



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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---|------------------|--|---|------|------|-------|---------|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | |
| Reverse recovery time | | $I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 21 | 26 | - |
| | | $I_F = 1.5 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 25 | 36 | |
| | t _{rr} | T _J = 25 °C | I _F = 15 A dI _F /dt = 200 A/μs V _R = 390 V | - | 29 | - | ns - |
| | | T _J = 125 °C | | - | 65 | - | |
| Bad was a second | , | T _J = 25 °C | | - | 3.9 | - | A |
| Peak recovery current | I _{RRM} | T _J = 125 °C | | - | 7.0 | - | |
| Reverse recovery charge | 0 | T _J = 25 °C | | - | 60 | - | nC |
| | Q_{rr} | T _J = 125 °C | | - | 240 | - | |
| Reverse recovery time | t _{rr} | T _J = 125 °C | I _F = 15 A dI _F /dt = 800 A/µs V _R = 390 V | - | 42 | - | ns |
| Peak recovery current | I _{RRM} | | | - | 21 | - | Α |
| Reverse recovery charge | Q _{rr} | | | - | 480 | - | nC |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|--|------------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | - 65 | - | 175 | °C |
| Thermal resistance, junction to case | R _{thJC} | R _{thJC} | | 1.3 | 1.51 | °C/W |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | | - | 70 | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | | 0.5 | - | |
| Weight | | | - | 2.0 | - | g |
| Weight | | | - | 0.07 | - | OZ. |
| Mounting torque | | | 6 (5) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking daying | | Case style D ² PAK | ETH1506SH | | | |
| Marking device | | Case style TO-262 | ETH1506-1H | | | |

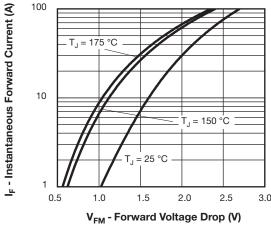


Fig. 1 - Typical Forward Voltage Drop Characteristics

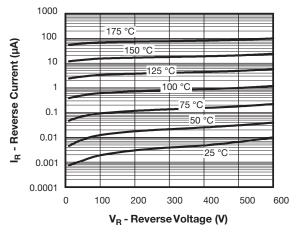


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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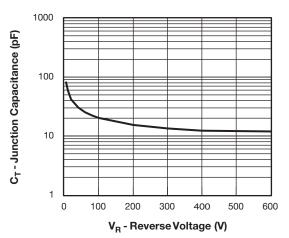


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

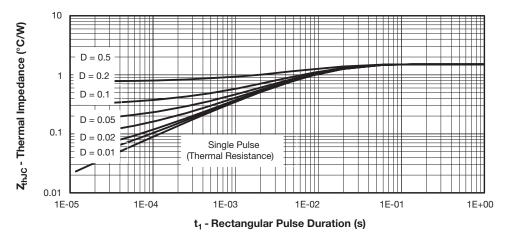


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

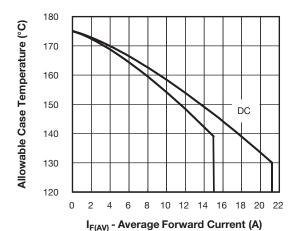


Fig. 5 - Maximum Allowable Case Temperature vs.

Average Forward Current

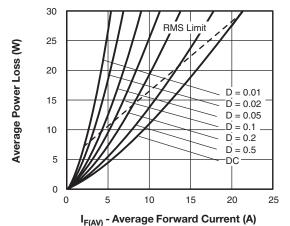


Fig. 6 - Forward Power Loss Characteristics

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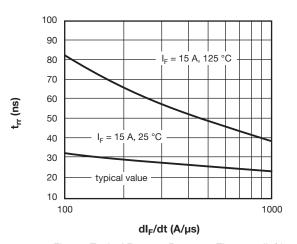


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

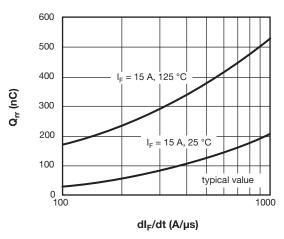


Fig. 8 - Typical Stored Charge vs. dl_F/dt

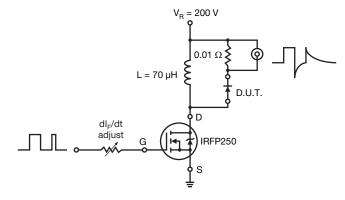
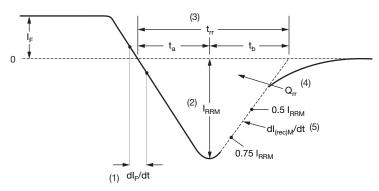


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

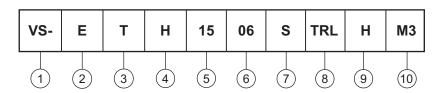


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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Circuit configuration
E = Single diode

- T = TO-220

H = Hyperfast recovery time

- Current code (15 = 15 A)

- Voltage code (06 = 600 V)

7 - • S = D²PAK

- • -1 = TO-262

8 - • None = Tube

- • TRL = Tape and reel (left oriented, for D²PAK package)

- • TRR = Tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

- Environmental digit:

M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|-------------------|------------------------|-------------------------|--|--|
| PREFERRED P/N | QUANTITY PER TUBE | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | |
| VS-ETH1506SHM3 | 50 | 1000 | Antistatic plastic tube | | |
| VS-ETH1506-1HM3 | 50 | 1000 | Antistatic plastic tube | | |
| VS-ETH1506STRRHM3 | 800 | 800 | 13" diameter reel | | |
| VS-ETH1506STRLHM3 | 800 | 800 | 13" diameter reel | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|--|-------------------------------|--------------------------|--|--|
| Dimensions TO-263AB (D ² PAK) <u>www.vishay.com/doc?95046</u> | | | | |
| Differisions | TO-262AA | www.vishay.com/doc?95419 | | |
| Part marking information | TO-263AB (D ² PAK) | www.vishay.com/doc?95444 | | |
| Part marking information | TO-262AA | www.vishay.com/doc?95443 | | |
| Packaging information | TO-263AB (D ² PAK) | www.vishay.com/doc?95032 | | |



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